

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,338,856 B2
APPLICATION NO. : 10/649050
DATED : March 4, 2008
INVENTOR(S) : Chen et al.

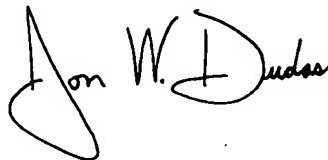
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It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 10, lines 56-58, in Claim 8, delete "introducing dopant atoms of the first type of dopant material into the first polysilicon layer" and insert -- forming the first polysilicon layer --, therefor.

Signed and Sealed this

Sixth Day of January, 2009

A handwritten signature in black ink, reading "Jon W. Dudas". The signature is stylized, with the first name "Jon" and last name "Dudas" clearly legible, and "W." in the middle.

JON W. DUDAS
Director of the United States Patent and Trademark Office